

# MBR2535CTLG

## Switch-mode Power Rectifier

### Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 25 A Total (12.5 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant\*

### Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

### Mechanical Characteristics

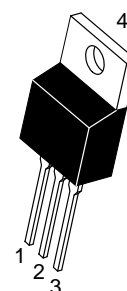
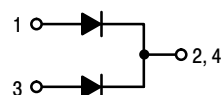
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B  
Machine Model C



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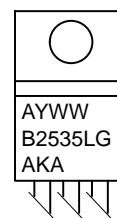
[www.onsemi.com](http://www.onsemi.com)

## SCHOTTKY BARRIER RECTIFIER 25 AMPERES, 35 VOLTS



TO-220  
CASE 221A  
STYLE 6

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
B2535L = Device Code  
G = Pb-Free Package  
AKA = Polarity Designator

### ORDERING INFORMATION

Device	Package	Shipping
MBR2535CTLG	TO-220 (Pb-Free)	50 Units/Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MBR2535CTLG

## MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	35	V
Average Rectified Forward Current ( $T_C = 142^\circ\text{C}$ per Diode) ( $T_C = 142^\circ\text{C}$ per Device)	$I_{F(AV)}$	12.5 25	A
Peak Repetitive Forward Current, per Leg (Sq Wave, 20 kHz, $T_C = 139^\circ\text{C}$ )	$I_{FRM}$	25	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	150	A
Peak Repetitive Reverse Surge Current (2.0 $\mu\text{s}$ , 1.0 kHz)	$I_{RRM}$	1.0	A
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature (Note 1)	$T_J$	-65 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$
Controlled Avalanche Energy	$W_{aval}$	20	mJ

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

## THERMAL CHARACTERISTICS

Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{\theta JC}$	2.0	$^\circ\text{C}/\text{W}$
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	$R_{\theta JA}$	75.0	

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2) ( $i_F = 25$ Amps, $T_j = 25^\circ\text{C}$ ) ( $i_F = 12.5$ Amps, $T_j = 25^\circ\text{C}$ ) ( $i_F = 12.5$ Amps, $T_j = 125^\circ\text{C}$ )	$V_F$	- - -	0.51 0.41 0.33	0.55 0.47 0.41	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_j = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_j = 125^\circ\text{C}$ )	$i_R$	- -	0.8 300	5.0 500	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

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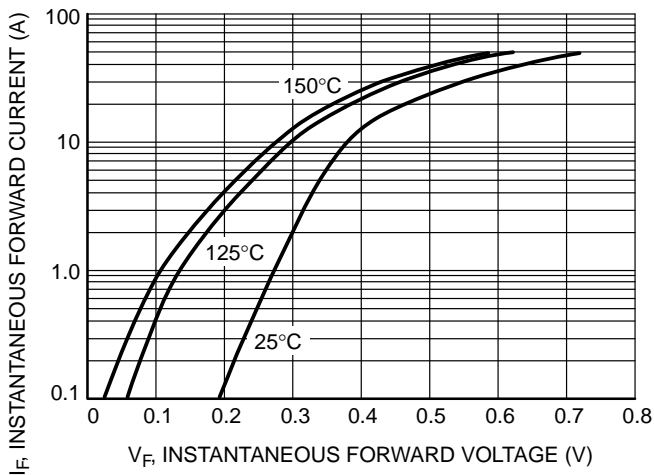


Figure 1. Typical Forward Voltage

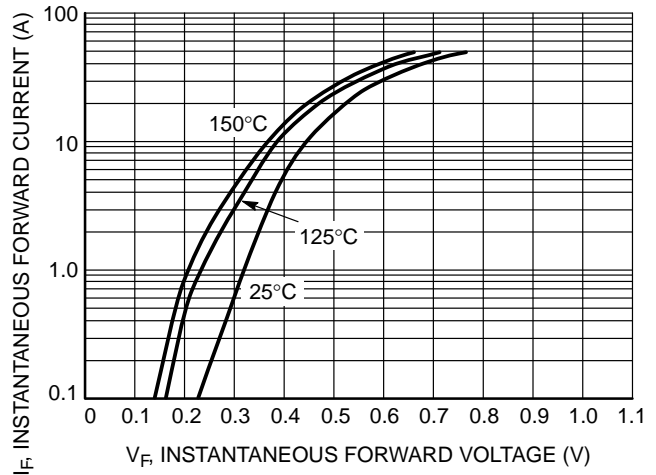


Figure 2. Maximum Forward Voltage

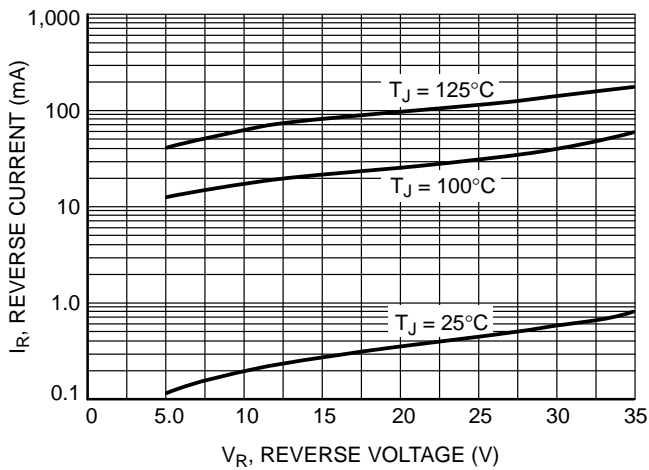


Figure 3. Typical Reverse Current, Per Leg

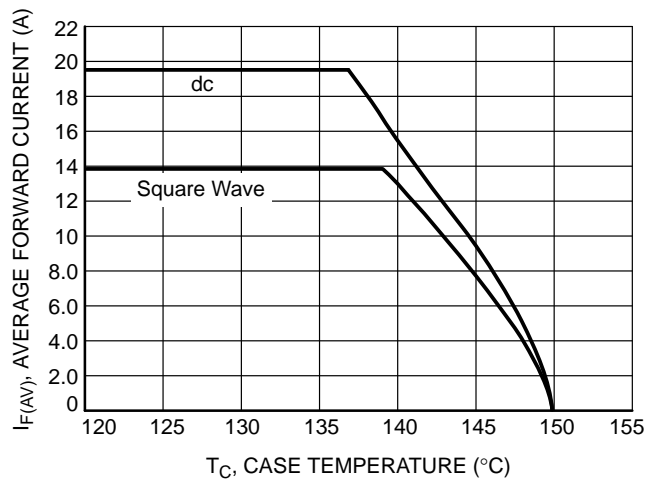


Figure 4. Current Derating, Case, Per Leg

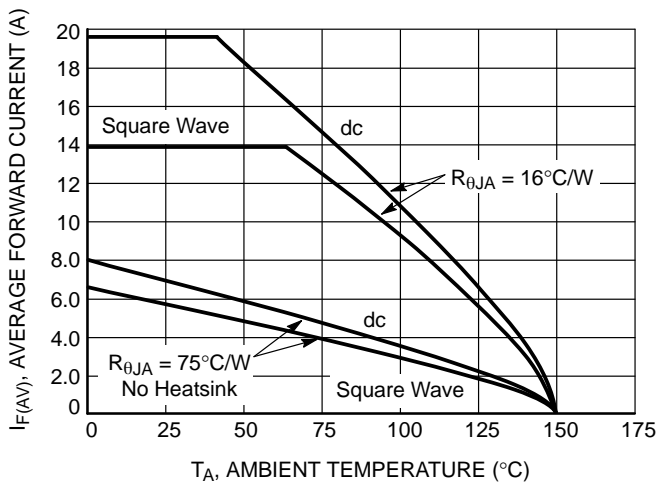


Figure 5. Current Derating, Ambient, Per Leg

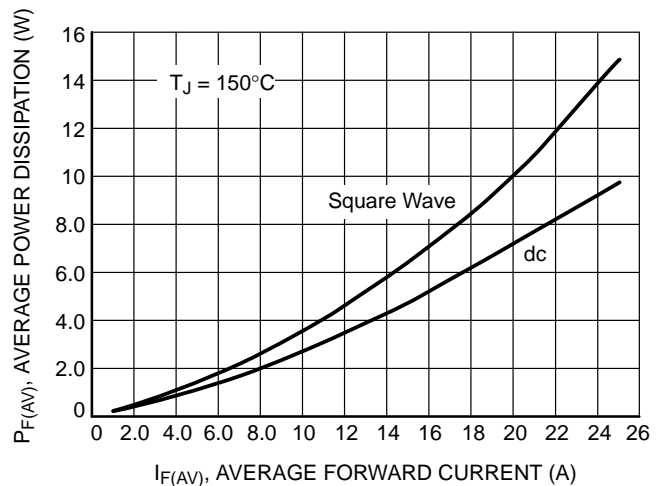
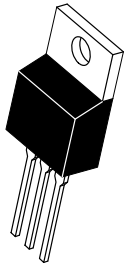


Figure 6. Forward Power Dissipation

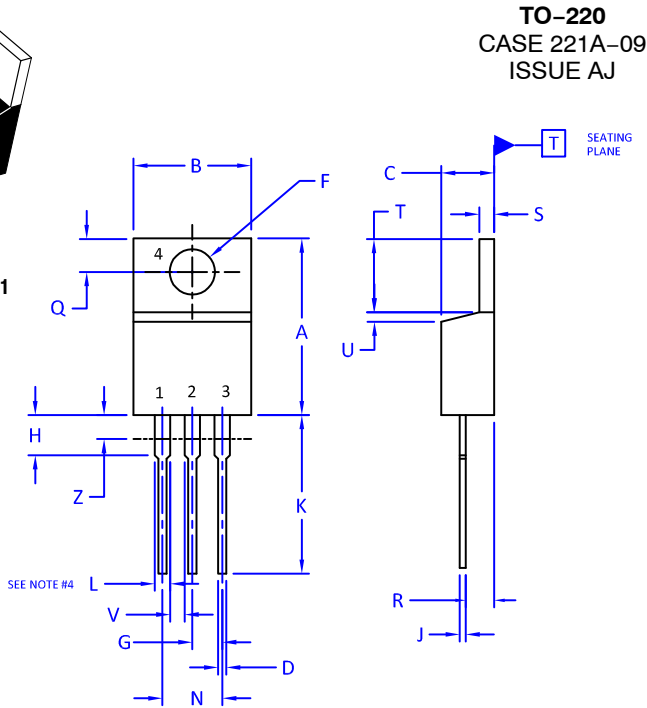
# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1



### TO-220 CASE 221A-09 ISSUE AJ

DATE 05 NOV 2019

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

**STYLE 1:**

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

**STYLE 2:**

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR
- 4. EMITTER

**STYLE 3:**

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

**STYLE 4:**

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

**STYLE 5:**

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

**STYLE 6:**

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

**STYLE 7:**

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

**STYLE 8:**

- PIN 1. CATHODE
- 2. ANODE
- 3. EXTERNAL TRIP/DELAY
- 4. ANODE

**STYLE 9:**

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

**STYLE 10:**

- PIN 1. GATE
- 2. SOURCE
- 3. DRAIN
- 4. SOURCE

**STYLE 11:**

- PIN 1. DRAIN
- 2. SOURCE
- 3. GATE
- 4. SOURCE

**STYLE 12:**

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. NOT CONNECTED

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